TD3F30MBL

Surface Mount Fast Recovery Bridge Rectifier Reverse Voltage - 1000 V Forward Current - 3 A

Features

- · Glass passivated chip junction
- Fast reverse recovery time
- Designed for Surface Mount Application

2 1 UMSB Package

DESCRIPTION
Input Pin (~)
Input Pin (~)

Output Anode (+)

Output Cathode (-)

PINNING

Mechanical Data

· Case: Molded plastic, UMSB

•Terminals: solderable per MIL-STD-750, Method 2026

Absolute Maximum Ratings and Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

December	Symbols	Value	Units	
Parameter	Marking	FMB30M.	-	
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	1000	V	
Maximum RMS Voltage	V_{RMS}	700	V	
Maximum DC Blocking Voltage	V_{DC}	1000	V	
Average Rectified Output Current T _C = 115°C	I _{F(AV)}	3	Α	
Peak Forward Surge Current 8.3 ms Single Half-sine-wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	100	А	
Peak Forward Surge Current 1 ms Single Half-square-wave Superimposed on Rated Load	I _{FSM}	180	А	
Maximum Forward Voltage at 3 A	V _F	1	V	
Maximum DC Reverse Current at Rated DC Blocking Voltage DC Blocking Voltage	I _R	0.5	μΑ	
Typical Junction Capacitance 1)	CJ	40	pF	
Typical Thermal Resistance 2)	R _{θJA}	35	°C/W	
Maximum Reverse Recovery Time 3)	t _{rr}	500	ns	
Operating Junction and Storage Temperature Range	T_{j},T_{stg}	- 55 to + 150	°C	

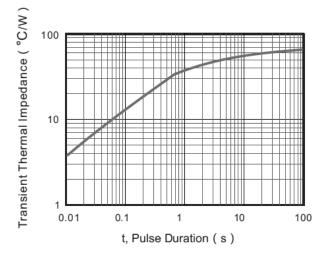
¹⁾ Measured at 1MHz and applied reverse voltage of 4 V D.C.

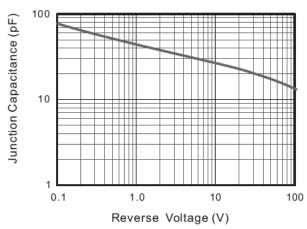


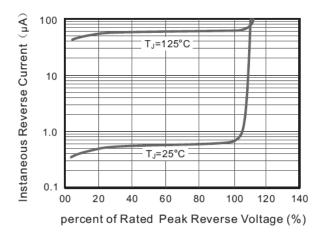
²⁾ Mounted on glass epoxy PC board with 4 x 1.5cm x1.5cm copper pad.

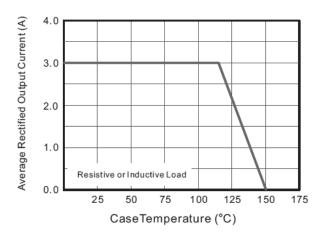
 $^{^{3)}}$ Measured with $I_{\textrm{F}}$ = 0.5 A, $I_{\textrm{R}}$ = 1 A, $I_{\textrm{rr}}$ = 0.25 A .

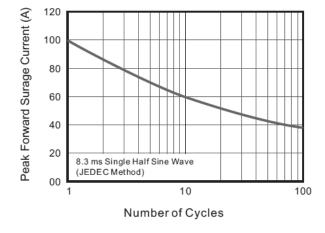
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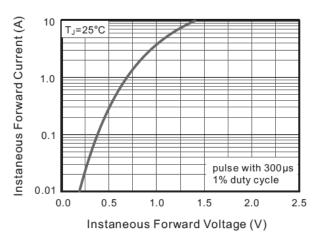








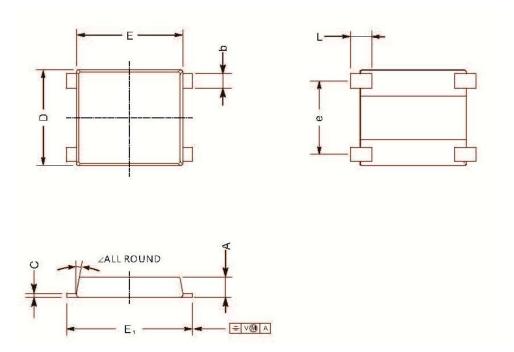






PACKAGE OUTLINE UMSB

Plastic surface mounted package; 4 leads



UNIT	Α	С	D	Е	E ₁	L	е	b	_
mm	1.5	0.29	7	7.6	8.9	1.6	5.3	1.15	10°
	1.3	0.17	6.2	7.1	7.9	1	4.9	0.95	10°